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Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	540
Number of Logic Elements/Cells	4320
Total RAM Bits	94208
Number of I/O	104
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	132-LFBGA, CSPBGA
Supplier Device Package	132-CSPBGA (8x8)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lcmxo2-4000ze-1mg132c

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MachXO2 Family Data Sheet Architecture

March 2016

Data Sheet DS1035

Architecture Overview

The MachXO2 family architecture contains an array of logic blocks surrounded by Programmable I/O (PIO). The larger logic density devices in this family have sysCLOCK[™] PLLs and blocks of sysMEM Embedded Block RAM (EBRs). Figure 2-1 and Figure 2-2 show the block diagrams of the various family members.





Note: MachXO2-256, and MachXO2-640/U are similar to MachXO2-1200. MachXO2-256 has a lower LUT count and no PLL or EBR blocks. MachXO2-640 has no PLL, a lower LUT count and two EBR blocks. MachXO2-640U has a lower LUT count, one PLL and seven EBR blocks.

Figure 2-2. Top View of the MachXO2-4000 Device



Note: MachXO2-1200U, MachXO2-2000/U and MachXO2-7000 are similar to MachXO2-4000. MachXO2-1200U and MachXO2-2000 have a lower LUT count, one PLL, and eight EBR blocks. MachXO2-2000U has a lower LUT count, two PLLs, and 10 EBR blocks. MachXO2-7000 has a higher LUT count, two PLLs, and 26 EBR blocks.

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The logic blocks, Programmable Functional Unit (PFU) and sysMEM EBR blocks, are arranged in a two-dimensional grid with rows and columns. Each row has either the logic blocks or the EBR blocks. The PIO cells are located at the periphery of the device, arranged in banks. The PFU contains the building blocks for logic, arithmetic, RAM, ROM, and register functions. The PIOs utilize a flexible I/O buffer referred to as a sysIO buffer that supports operation with a variety of interface standards. The blocks are connected with many vertical and horizontal routing channel resources. The place and route software tool automatically allocates these routing resources.

In the MachXO2 family, the number of sysIO banks varies by device. There are different types of I/O buffers on the different banks. Refer to the details in later sections of this document. The sysMEM EBRs are large, dedicated fast memory blocks; these blocks are found in MachXO2-640/U and larger devices. These blocks can be configured as RAM, ROM or FIFO. FIFO support includes dedicated FIFO pointer and flag "hard" control logic to minimize LUT usage.

The MachXO2 registers in PFU and sysl/O can be configured to be SET or RESET. After power up and device is configured, the device enters into user mode with these registers SET/RESET according to the configuration setting, allowing device entering to a known state for predictable system function.

The MachXO2 architecture also provides up to two sysCLOCK Phase Locked Loop (PLL) blocks on MachXO2-640U, MachXO2-1200/U and larger devices. These blocks are located at the ends of the on-chip Flash block. The PLLs have multiply, divide, and phase shifting capabilities that are used to manage the frequency and phase relationships of the clocks.

MachXO2 devices provide commonly used hardened functions such as SPI controller, I²C controller and timer/ counter. MachXO2-640/U and higher density devices also provide User Flash Memory (UFM). These hardened functions and the UFM interface to the core logic and routing through a WISHBONE interface. The UFM can also be accessed through the SPI, I²C and JTAG ports.

Every device in the family has a JTAG port that supports programming and configuration of the device as well as access to the user logic. The MachXO2 devices are available for operation from 3.3 V, 2.5 V and 1.2 V power supplies, providing easy integration into the overall system.

PFU Blocks

The core of the MachXO2 device consists of PFU blocks, which can be programmed to perform logic, arithmetic, distributed RAM and distributed ROM functions. Each PFU block consists of four interconnected slices numbered 0 to 3 as shown in Figure 2-3. Each slice contains two LUTs and two registers. There are 53 inputs and 25 outputs associated with each PFU block.



Figure 2-4. Slice Diagram



For Slices 0 and 1, memory control signals are generated from Slice 2 as follows:

- WCK is CLK
 WRE is from LSR
- DI[3:2] for Slice 1 and DI[1:0] for Slice 0 data from Slice 2
- WAD [A:D] is a 4-bit address from slice 2 LUT input

 Table 2-2. Slice Signal Descriptions

Function	Туре	Signal Names	Description
Input	Data signal	A0, B0, C0, D0	Inputs to LUT4
Input	Data signal	A1, B1, C1, D1	Inputs to LUT4
Input	Multi-purpose	M0/M1	Multi-purpose input
Input	Control signal	CE	Clock enable
Input	Control signal	LSR	Local set/reset
Input	Control signal	CLK	System clock
Input	Inter-PFU signal	FCIN	Fast carry in ¹
Output	Data signals	F0, F1	LUT4 output register bypass signals
Output	Data signals	Q0, Q1	Register outputs
Output	Data signals	OFX0	Output of a LUT5 MUX
Output	Data signals	OFX1	Output of a LUT6, LUT7, LUT8 ² MUX depending on the slice
Output	Inter-PFU signal	FCO	Fast carry out ¹

1. See Figure 2-3 for connection details.

2. Requires two PFUs.



Programmable I/O Cells (PIC)

The programmable logic associated with an I/O is called a PIO. The individual PIO are connected to their respective sysIO buffers and pads. On the MachXO2 devices, the PIO cells are assembled into groups of four PIO cells called a Programmable I/O Cell or PIC. The PICs are placed on all four sides of the device.

On all the MachXO2 devices, two adjacent PIOs can be combined to provide a complementary output driver pair.

The MachXO2-640U, MachXO2-1200/U and higher density devices contain enhanced I/O capability. All PIO pairs on these larger devices can implement differential receivers. Half of the PIO pairs on the top edge of these devices can be configured as true LVDS transmit pairs. The PIO pairs on the bottom edge of these higher density devices have on-chip differential termination and also provide PCI support.



Output Register Block

The output register block registers signals from the core of the device before they are passed to the sysIO buffers.

Left, Top, Bottom Edges

In SDR mode, D0 feeds one of the flip-flops that then feeds the output. The flip-flop can be configured as a D-type register or latch.

In DDR generic mode, D0 and D1 inputs are fed into registers on the positive edge of the clock. At the next falling edge the registered D1 input is registered into the register Q1. A multiplexer running off the same clock is used to switch the mux between the outputs of registers Q0 and Q1 that will then feed the output.

Figure 2-14 shows the output register block on the left, top and bottom edges.

Figure 2-14. MachXO2 Output Register Block Diagram (PIO on the Left, Top and Bottom Edges)



Right Edge

The output register block on the right edge is a superset of the output register on left, top and bottom edges of the device. In addition to supporting SDR and Generic DDR modes, the output register blocks for PIOs on the right edge include additional logic to support DDR-memory interfaces. Operation of this block is similar to that of the output register block on other edges.

In DDR memory mode, D0 and D1 inputs are fed into registers on the positive edge of the clock. At the next falling edge the registered D1 input is registered into the register Q1. A multiplexer running off the DQSW90 signal is used to switch the mux between the outputs of registers Q0 and Q1 that will then feed the output.

Figure 2-15 shows the output register block on the right edge.



These gearboxes have three stage pipeline registers. The first stage registers sample the high-speed input data by the high-speed edge clock on its rising and falling edges. The second stage registers perform data alignment based on the control signals UPDATE and SEL0 from the control block. The third stage pipeline registers pass the data to the device core synchronized to the low-speed system clock. Figure 2-16 shows a block diagram of the input gearbox.

Figure 2-16. Input Gearbox





For more details on these embedded functions, please refer to TN1205, Using User Flash Memory and Hardened Control Functions in MachXO2 Devices.

User Flash Memory (UFM)

MachXO2-640/U and higher density devices provide a User Flash Memory block, which can be used for a variety of applications including storing a portion of the configuration image, initializing EBRs, to store PROM data or, as a general purpose user Flash memory. The UFM block connects to the device core through the embedded function block WISHBONE interface. Users can also access the UFM block through the JTAG, I²C and SPI interfaces of the device. The UFM block offers the following features:

- Non-volatile storage up to 256 kbits
- 100K write cycles
- Write access is performed page-wise; each page has 128 bits (16 bytes)
- Auto-increment addressing
- WISHBONE interface

For more information on the UFM, please refer to TN1205, Using User Flash Memory and Hardened Control Functions in MachXO2 Devices.

Standby Mode and Power Saving Options

MachXO2 devices are available in three options for maximum flexibility: ZE, HC and HE devices. The ZE devices have ultra low static and dynamic power consumption. These devices use a 1.2 V core voltage that further reduces power consumption. The HC and HE devices are designed to provide high performance. The HC devices have a built-in voltage regulator to allow for 2.5 V V_{CC} and 3.3 V V_{CC} while the HE devices operate at 1.2 V V_{CC}.

MachXO2 devices have been designed with features that allow users to meet the static and dynamic power requirements of their applications by controlling various device subsystems such as the bandgap, power-on-reset circuitry, I/O bank controllers, power guard, on-chip oscillator, PLLs, etc. In order to maximize power savings, MachXO2 devices support an ultra low power Stand-by mode. While most of these features are available in all three device types, these features are mainly intended for use with MachXO2 ZE devices to manage power consumption.

In the stand-by mode the MachXO2 devices are powered on and configured. Internal logic, I/Os and memories are switched on and remain operational, as the user logic waits for an external input. The device enters this mode when the standby input of the standby controller is toggled or when an appropriate I²C or JTAG instruction is issued by an external master. Various subsystems in the device such as the band gap, power-on-reset circuitry etc can be configured such that they are automatically turned "off" or go into a low power consumption state to save power when the device enters this state. Note that the MachXO2 devices are powered on when in standby mode and all power supplies should remain in the Recommended Operating Conditions.



Device Subsystem	Feature Description
Bandgap	The bandgap can be turned off in standby mode. When the Bandgap is turned off, ana- log circuitry such as the POR, PLLs, on-chip oscillator, and referenced and differential I/O buffers are also turned off. Bandgap can only be turned off for 1.2 V devices.
Power-On-Reset (POR)	The POR can be turned off in standby mode. This monitors VCC levels. In the event of unsafe V_{CC} drops, this circuit reconfigures the device. When the POR circuitry is turned off, limited power detector circuitry is still active. This option is only recommended for applications in which the power supply rails are reliable.
On-Chip Oscillator	The on-chip oscillator has two power saving features. It may be switched off if it is not needed in your design. It can also be turned off in Standby mode.
PLL	Similar to the on-chip oscillator, the PLL also has two power saving features. It can be statically switched off if it is not needed in a design. It can also be turned off in Standby mode. The PLL will wait until all output clocks from the PLL are driven low before powering off.
I/O Bank Controller	Referenced and differential I/O buffers (used to implement standards such as HSTL, SSTL and LVDS) consume more than ratioed single-ended I/Os such as LVCMOS and LVTTL. The I/O bank controller allows the user to turn these I/Os off dynamically on a per bank selection.
Dynamic Clock Enable for Primary Clock Nets	Each primary clock net can be dynamically disabled to save power.
Power Guard	Power Guard is a feature implemented in input buffers. This feature allows users to switch off the input buffer when it is not needed. This feature can be used in both clock and data paths. Its biggest impact is that in the standby mode it can be used to switch off clock inputs that are distributed using general routing resources.

For more details on the standby mode refer to TN1198, Power Estimation and Management for MachXO2 Devices.

Power On Reset

MachXO2 devices have power-on reset circuitry to monitor V_{CCINT} and V_{CCIO} voltage levels during power-up and operation. At power-up, the POR circuitry monitors V_{CCINT} and V_{CCIO0} (controls configuration) voltage levels. It then triggers download from the on-chip configuration Flash memory after reaching the V_{PORUP} level specified in the Power-On-Reset Voltage table in the DC and Switching Characteristics section of this data sheet. For devices without voltage regulators (ZE and HE devices), V_{CCINT} is the same as the V_{CC} supply voltage. For devices with voltage regulators (HC devices), V_{CCINT} is regulated from the V_{CC} supply voltage. From this voltage reference, the time taken for configuration and entry into user mode is specified as Flash Download Time (t_{REFRESH}) in the DC and Switching Characteristics section of this data sheet. Before and during configuration, the I/Os are held in tristate. I/Os are released to user functionality once the device has finished configuration. Note that for HC devices, a separate POR circuit monitors external V_{CC} voltage in addition to the POR circuit that monitors the internal post-regulated power supply voltage level.

Once the device enters into user mode, the POR circuitry can optionally continue to monitor V_{CCINT} levels. If V_{CCINT} drops below $V_{PORDNBG}$ level (with the bandgap circuitry switched on) or below $V_{PORDNSRAM}$ level (with the bandgap circuitry switched off to conserve power) device functionality cannot be guaranteed. In such a situation the POR issues a reset and begins monitoring the V_{CCINT} and V_{CCIO} voltage levels. $V_{PORDNBG}$ and $V_{PORDNSRAM}$ are both specified in the Power-On-Reset Voltage table in the DC and Switching Characteristics section of this data sheet.

Note that once a ZE or HE device enters user mode, users can switch off the bandgap to conserve power. When the bandgap circuitry is switched off, the POR circuitry also shuts down. The device is designed such that a minimal, low power POR circuit is still operational (this corresponds to the $V_{PORDNSRAM}$ reset point described in the paragraph above). However this circuit is not as accurate as the one that operates when the bandgap is switched on. The low power POR circuit emulates an SRAM cell and is biased to trip before the vast majority of SRAM cells flip. If users are concerned about the V_{CC} supply dropping below V_{CC} (min) they should not shut down the bandgap or POR circuit.



MachXO2 Family Data Sheet DC and Switching Characteristics

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Absolute Maximum Ratings^{1, 2, 3}

	MachXO2 ZE/HE (1.2 V)	MachXO2 HC (2.5 V / 3.3 V)
Supply Voltage V _{CC}	–0.5 V to 1.32 V	–0.5 V to 3.75 V
Output Supply Voltage V _{CCIO}	–0.5 V to 3.75 V	–0.5 V to 3.75 V
I/O Tri-state Voltage Applied ^{4, 5}	–0.5 V to 3.75 V	–0.5 V to 3.75 V
Dedicated Input Voltage Applied ⁴	–0.5 V to 3.75 V	–0.5 V to 3.75 V
Storage Temperature (Ambient)	–55 °C to 125 °C	–55 °C to 125 °C
Junction Temperature (T _J)	–40 °C to 125 °C	–40 °C to 125 °C

1. Stress above those listed under the "Absolute Maximum Ratings" may cause permanent damage to the device. Functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

2. Compliance with the Lattice Thermal Management document is required.

3. All voltages referenced to GND.

4. Overshoot and undershoot of -2 V to (V_{IHMAX} + 2) volts is permitted for a duration of <20 ns.

5. The dual function I^2C pins SCL and SDA are limited to -0.25 V to 3.75 V or to -0.3 V with a duration of <20 ns.

Recommended Operating Conditions¹

Symbol	Parameter	Min.	Max.	Units
V _{CC} ¹	Core Supply Voltage for 1.2 V Devices	1.14	1.26	V
VCC	Core Supply Voltage for 2.5 V / 3.3 V Devices	2.375	3.6	V
V _{CCIO} ^{1, 2, 3}	I/O Driver Supply Voltage	1.14	3.6	V
t _{JCOM}	Junction Temperature Commercial Operation	0	85	°C
t _{JIND}	Junction Temperature Industrial Operation	-40	100	°C

1. Like power supplies must be tied together. For example, if V_{CCIO} and V_{CC} are both the same voltage, they must also be the same supply.

2. See recommended voltages by I/O standard in subsequent table.

3. V_{CCIO} pins of unused I/O banks should be connected to the V_{CC} power supply on boards.

Power Supply Ramp Rates¹

Symbol	Parameter	Min.	Тур.	Max.	Units
t _{RAMP}	Power supply ramp rates for all power supplies.	0.01		100	V/ms

1. Assumes monotonic ramp rates.

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Power-On-Reset Voltage Levels^{1, 2, 3, 4, 5}

Symbol	Parameter	Min.	Тур.	Max.	Units
V _{PORUP}	Power-On-Reset ramp up trip point (band gap based circuit monitoring V_{CCINT} and $V_{CCIO0})$	0.9	_	1.06	V
V _{PORUPEXT}	Power-On-Reset ramp up trip point (band gap based circuit monitoring external V_{CC} power supply)	1.5	_	2.1	V
V _{PORDNBG}	Power-On-Reset ramp down trip point (band gap based circuit monitoring $V_{CCINT})$	0.75	_	0.93	V
V _{PORDNBGEXT}	Power-On-Reset ramp down trip point (band gap based circuit monitoring V_{CC})	0.98	_	1.33	V
V _{PORDNSRAM}	Power-On-Reset ramp down trip point (SRAM based circuit monitoring $V_{CCINT})$	_	0.6		V
V _{PORDNSRAMEXT}	Power-On-Reset ramp down trip point (SRAM based circuit monitoring V_{CC})	_	0.96	—	V

1. These POR trip points are only provided for guidance. Device operation is only characterized for power supply voltages specified under recommended operating conditions.

2. For devices without voltage regulators V_{CCINT} is the same as the V_{CC} supply voltage. For devices with voltage regulators, V_{CCINT} is regulated from the V_{CC} supply voltage.

3. Note that V_{PORUP} (min.) and V_{PORDNBG} (max.) are in different process corners. For any given process corner V_{PORDNBG} (max.) is always 12.0 mV below V_{PORUP} (min.).

4. V_{PORUPEXT} is for HC devices only. In these devices a separate POR circuit monitors the external V_{CC} power supply.

5. V_{CCIO0} does not have a Power-On-Reset ramp down trip point. V_{CCIO0} must remain within the Recommended Operating Conditions to ensure proper operation.

Programming/Erase Specifications

Symbol	Parameter	Min.	Max. ¹	Units	
Nanagaya	Flash Programming cycles per t _{RETENTION}	—	10,000	Cycles	
NPROGCYC	Flash functional programming cycles	—	100,000		
	Data retention at 100 °C junction temperature	10	—	Years	
RETENTION	Data retention at 85 °C junction temperature	20	_	Teals	

1. Maximum Flash memory reads are limited to 7.5E13 cycles over the lifetime of the product.

Hot Socketing Specifications^{1, 2, 3}

Symbol	Parameter	Condition	Max.	Units
I _{DK}	Input or I/O leakage Current	$0 < V_{IN} < V_{IH}$ (MAX)	+/-1000	μΑ

1. Insensitive to sequence of V_{CC} and V_{CCIO} . However, assumes monotonic rise/fall rates for V_{CC} and V_{CCIO} .

2. $0 < V_{CC} < V_{CC}$ (MAX), $0 < V_{CCIO} < V_{CCIO}$ (MAX).

3. I_{DK} is additive to I_{PU}, I_{PD} or I_{BH}.

ESD Performance

Please refer to the MachXO2 Product Family Qualification Summary for complete qualification data, including ESD performance.



Typical Building Block Function Performance – HC/HE Devices¹

Pin-to-Pin Performance (LVCMOS25 12 mA Drive)

Function	-6 Timing	Units
Basic Functions		
16-bit decoder	8.9	ns
4:1 MUX	7.5	ns
16:1 MUX	8.3	ns

Register-to-Register Performance

Function	-6 Timing	Units
Basic Functions		
16:1 MUX	412	MHz
16-bit adder	297	MHz
16-bit counter	324	MHz
64-bit counter	161	MHz
Embedded Memory Functions		
1024x9 True-Dual Port RAM (Write Through or Normal, EBR output registers)	183	MHz
Distributed Memory Functions		
16x4 Pseudo-Dual Port RAM (one PFU)	500	MHz

 The above timing numbers are generated using the Diamond design tool. Exact performance may vary with device and tool version. The tool uses internal parameters that have been characterized but are not tested on every device. Commercial timing numbers are shown at 85 °C and 1.14 V. Other operating conditions, including industrial, can be extracted from the Diamond software.



Maximum sysIO Buffer Performance

I/O Standard	Max. Speed	Units
LVDS25	400	MHz
LVDS25E	150	MHz
RSDS25	150	MHz
RSDS25E	150	MHz
BLVDS25	150	MHz
BLVDS25E	150	MHz
MLVDS25	150	MHz
MLVDS25E	150	MHz
LVPECL33	150	MHz
LVPECL33E	150	MHz
SSTL25_I	150	MHz
SSTL25_II	150	MHz
SSTL25D_I	150	MHz
SSTL25D_II	150	MHz
SSTL18_I	150	MHz
SSTL18_II	150	MHz
SSTL18D_I	150	MHz
SSTL18D_II	150	MHz
HSTL18_I	150	MHz
HSTL18_II	150	MHz
HSTL18D_I	150	MHz
HSTL18D_II	150	MHz
PCI33	134	MHz
LVTTL33	150	MHz
LVTTL33D	150	MHz
LVCMOS33	150	MHz
LVCMOS33D	150	MHz
LVCMOS25	150	MHz
LVCMOS25D	150	MHz
LVCMOS25R33	150	MHz
LVCMOS18	150	MHz
LVCMOS18D	150	MHz
LVCMOS18R33	150	MHz
LVCMOS18R25	150	MHz
LVCMOS15	150	MHz
LVCMOS15D	150	MHz
LVCMOS15R33	150	MHz
LVCMOS15R25	150	MHz
LVCMOS12	91	MHz
LVCMOS12D	91	MHz



			-3		_	-2	_	-1	
Parameter	Description	Device	Min.	Max.	Min.	Max.	Min.	Max.	Units
LPDDR ^{9, 12}		•							1
t _{DVADQ}	Input Data Valid After DQS Input		_	0.349	_	0.381	_	0.396	UI
t _{DVEDQ}	Input Data Hold After DQS Input		0.665	—	0.630	_	0.613	—	UI
t _{DQVBS}	Output Data Invalid Before DQS Output	MachXO2-1200/U	0.25	—	0.25	_	0.25	—	UI
t _{DQVAS}	Output Data Invalid After DQS Output	and larger devices, right side only. ¹³	0.25	_	0.25	_	0.25	_	UI
f _{DATA}	MEM LPDDR Serial Data Speed		_	120	_	110	_	96	Mbps
f _{SCLK}	SCLK Frequency		—	60	—	55	_	48	MHz
f _{LPDDR}	LPDDR Data Transfer Rate		0	120	0	110	0	96	Mbps
DDR ^{9, 12}			•				•	•	
t _{DVADQ}	Input Data Valid After DQS Input		_	0.347	_	0.374	_	0.393	UI
t _{DVEDQ}	Input Data Hold After DQS Input		0.665	_	0.637	_	0.616	—	UI
t _{DQVBS}	Output Data Invalid Before DQS Output	MachXO2-1200/U and larger devices,	0.25	_	0.25	_	0.25	—	UI
t _{DQVAS}	Output Data Invalid After DQS Output	right side only. ¹³	0.25	_	0.25	_	0.25	_	UI
f _{DATA}	MEM DDR Serial Data Speed			140		116		98	Mbps
f _{SCLK}	SCLK Frequency		—	70	—	58	—	49	MHz
f _{MEM_DDR}	MEM DDR Data Transfer Rate		N/A	140	N/A	116	N/A	98	Mbps
DDR2 ^{9, 12}		•							
t _{DVADQ}	Input Data Valid After DQS Input		_	0.372	_	0.394	_	0.410	UI
t _{DVEDQ}	Input Data Hold After DQS Input		0.690	_	0.658	_	0.618	_	UI
t _{DQVBS}	Output Data Invalid Before DQS Output	MachXO2-1200/U	0.25	_	0.25	_	0.25	_	UI
t _{DQVAS}	Output Data Invalid After DQS Output	and larger devices, right side only. ¹³	0.25	_	0.25	_	0.25		UI
f _{DATA}	MEM DDR Serial Data Speed	1	—	140	—	116		98	Mbps
f _{SCLK}	SCLK Frequency	1	—	70	—	58		49	MHz
f _{MEM_DDR2}	MEM DDR2 Data Transfer Rate		N/A	140	N/A	116	N/A	98	Mbps

1. Exact performance may vary with device and design implementation. Commercial timing numbers are shown at 85 °C and 1.14 V. Other operating conditions, including industrial, can be extracted from the Diamond software.

2. General I/O timing numbers based on LVCMOS 2.5, 8 mA, 0 pf load, fast slew rate.

3. Generic DDR timing numbers based on LVDS I/O (for input, output, and clock ports).

4. DDR timing numbers based on SSTL25. DDR2 timing numbers based on SSTL18. LPDDR timing numbers based in LVCMOS18.

5. 7:1 LVDS (GDDR71) uses the LVDS I/O standard (for input, output, and clock ports).

6. For Generic DDRX1 mode $t_{SU} = t_{HO} = (t_{DVE} - t_{DVA} - 0.03 \text{ ns})/2$.

7. The $t_{SU_{DEL}}$ and $t_{H_{DEL}}$ values use the SCLK_ZERHOLD default step size. Each step is 167 ps (-3), 182 ps (-2), 195 ps (-1).

8. This number for general purpose usage. Duty cycle tolerance is +/-10%.

9. Duty cycle is +/-5% for system usage.

10. The above timing numbers are generated using the Diamond design tool. Exact performance may vary with the device selected.

11. High-speed DDR and LVDS not supported in SG32 (32-Pin QFN) packages.

12. Advance information for MachXO2 devices in 48 QFN packages.

13. DDR memory interface not supported in QN84 (84 QFN) and SG32 (32 QFN) packages.



Signal Descriptions (Cont.)

Signal Name	I/O	Descriptions
INITN	I/O	Open Drain pin. Indicates the FPGA is ready to be configured. During configuration, or when reserved as INITn in user mode, this pin has an active pull-up.
DONE	I/O	Open Drain pin. Indicates that the configuration sequence is complete, and the start-up sequence is in progress. During configuration, or when reserved as DONE in user mode, this pin has an active pull-up.
MCLK/CCLK	I/O	Input Configuration Clock for configuring an FPGA in Slave SPI mode. Output Configuration Clock for configuring an FPGA in SPI and SPIm configuration modes.
SN	I	Slave SPI active low chip select input.
CSSPIN	I/O	Master SPI active low chip select output.
SI/SPISI	I/O	Slave SPI serial data input and master SPI serial data output.
SO/SPISO	I/O	Slave SPI serial data output and master SPI serial data input.
SCL	I/O	Slave I ² C clock input and master I ² C clock output.
SDA	I/O	Slave I ² C data input and master I ² C data output.





			MachXO2-1200U			
	100 TQFP	132 csBGA	144 TQFP	25 WLCSP	32 QFN ¹	256 ftBGA
General Purpose I/O per Bank	•					
Bank 0	18	25	27	11	9	50
Bank 1	21	26	26	0	2	52
Bank 2	20	28	28	7	9	52
Bank 3	20	25	26	0	2	16
Bank 4	0	0	0	0	0	16
Bank 5	0	0	0	0	0	20
Total General Purpose Single Ended I/O	79	104	107	18	22	206
Differential I/O per Bank						
Bank 0	9	13	14	5	4	25
Bank 1	10	13	13	0	1	26
Bank 2	10	14	14	2	4	26
Bank 3	10	12	13	0	1	8
Bank 4	0	0	0	0	0	8
Bank 5	0	0	0	0	0	10
Total General Purpose Differential I/O	39	52	54	7	10	103
Dual Function I/O	31	33	33	18	22	33
High-speed Differential I/O						
Bank 0	4	7	7	0	0	14
Gearboxes						
Number of 7:1 or 8:1 Output Gearbox Available (Bank 0)	4	7	7	0	0	14
Number of 7:1 or 8:1 Input Gearbox Avail- able (Bank 2)	5	7	7	0	2	14
DQS Groups						
Bank 1	1	2	2	0	0	2
VCCIO Pins						
Bank 0	2	3	3	1	2	4
Bank 1	2	3	3	0	1	4
Bank 2	2	3	3	1	2	4
Bank 3	3	3	3	0	1	1
Bank 4	0	0	0	0	0	2
Bank 5	0	0	0	0	0	1
VCC	2	4	4	2	2	8
GND	8	10	12	2	2	24
NC	1	1	8	0	0	1
Reserved for Configuration	1	1	1	1	1	1
Total Count of Bonded Pins	100	132	144	25	32	256
1. Lattice recommends soldering the centra						

1. Lattice recommends soldering the central thermal pad onto the top PCB ground for improved thermal resistance.



			MachX	02-2000			MachXO2-2000U
	49 WLCSP	100 TQFP	132 csBGA	144 TQFP	256 caBGA	256 ftBGA	484 ftBGA
General Purpose I/O per Bank	•		•		•		
Bank 0	19	18	25	27	50	50	70
Bank 1	0	21	26	28	52	52	68
Bank 2	13	20	28	28	52	52	72
Bank 3	0	6	7	8	16	16	24
Bank 4	0	6	8	10	16	16	16
Bank 5	6	8	10	10	20	20	28
Total General Purpose Single-Ended I/O	38	79	104	111	206	206	278
Differential I/O per Bank							
Bank 0	7	9	13	14	25	25	35
Bank 1	0	10	13	14	26	26	34
Bank 2	6	10	14	14	26	26	36
Bank 3	0	3	3	4	8	8	12
Bank 4	0	3	4	5	8	8	8
Bank 5	3	4	5	5	10	10	14
Total General Purpose Differential I/O	16	39	52	56	103	103	139
Dual Function I/O	24	31	33	33	33	33	37
High-speed Differential I/O		-					_
Bank 0	5	4	8	9	14	14	18
Gearboxes	-		_	_			-
Number of 7:1 or 8:1 Output Gearbox Available (Bank 0)	5	4	8	9	14	14	18
Number of 7:1 or 8:1 Input Gearbox Available (Bank 2)	6	10	14	14	14	14	18
DQS Groups							
Bank 1	0	1	2	2	2	2	2
VCCIO Pins							
Bank 0	2	2	3	3	4	4	10
Bank 1	0	2	3	3	4	4	10
Bank 2	1	2	3	3	4	4	10
Bank 3	0	1	1	1	1	1	3
Bank 4	0	1	1	1	2	2	4
Bank 5	1	1	1	1	1	1	3
			1		1	r	T
VCC	2	2	4	4	8	8	12
GND	4	8	10	12	24	24	48
NC	0	1	1	4	1	1	105
Reserved for Configuration	1	1	1	1	v	1	1
Total Count of Bonded Pins	39	100	132	144	256	256	484



MachXO2 Family Data Sheet Ordering Information

March 2017

Data Sheet DS1035

MachXO2 Part Number Description



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Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-4000HE-6BG332C	4320	1.2 V	-6	Halogen-Free caBGA	332	COM
LCMXO2-4000HE-4FG484C	4320	1.2 V	-4	Halogen-Free fpBGA	484	COM
LCMXO2-4000HE-5FG484C	4320	1.2 V	-5	Halogen-Free fpBGA	484	COM
LCMXO2-4000HE-6FG484C	4320	1.2 V	-6	Halogen-Free fpBGA	484	COM

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-7000HE-4TG144C	6864	1.2 V	-4	Halogen-Free TQFP	144	COM
LCMXO2-7000HE-5TG144C	6864	1.2 V	-5	Halogen-Free TQFP	144	COM
LCMXO2-7000HE-6TG144C	6864	1.2 V	-6	Halogen-Free TQFP	144	COM
LCMXO2-7000HE-4BG256C	6864	1.2 V	-4	Halogen-Free caBGA	256	COM
LCMXO2-7000HE-5BG256C	6864	1.2 V	-5	Halogen-Free caBGA	256	COM
LCMXO2-7000HE-6BG256C	6864	1.2 V	-6	Halogen-Free caBGA	256	COM
LCMXO2-7000HE-4FTG256C	6864	1.2 V	-4	Halogen-Free ftBGA	256	COM
LCMXO2-7000HE-5FTG256C	6864	1.2 V	-5	Halogen-Free ftBGA	256	COM
LCMXO2-7000HE-6FTG256C	6864	1.2 V	-6	Halogen-Free ftBGA	256	COM
LCMXO2-7000HE-4BG332C	6864	1.2 V	-4	Halogen-Free caBGA	332	COM
LCMXO2-7000HE-5BG332C	6864	1.2 V	-5	Halogen-Free caBGA	332	COM
LCMXO2-7000HE-6BG332C	6864	1.2 V	-6	Halogen-Free caBGA	332	COM
LCMXO2-7000HE-4FG484C	6864	1.2 V	-4	Halogen-Free fpBGA	484	COM
LCMXO2-7000HE-5FG484C	6864	1.2 V	-5	Halogen-Free fpBGA	484	COM
LCMXO2-7000HE-6FG484C	6864	1.2 V	-6	Halogen-Free fpBGA	484	COM



Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-4000HC-4QN84I	4320	2.5 V / 3.3 V	-4	Halogen-Free QFN	84	IND
LCMXO2-4000HC-5QN84I	4320	2.5 V / 3.3 V	-5	Halogen-Free QFN	84	IND
LCMXO2-4000HC-6QN84I	4320	2.5 V / 3.3 V	-6	Halogen-Free QFN	84	IND
LCMXO2-4000HC-4TG144I	4320	2.5 V / 3.3 V	-4	Halogen-Free TQFP	144	IND
LCMXO2-4000HC-5TG144I	4320	2.5 V / 3.3 V	-5	Halogen-Free TQFP	144	IND
LCMXO2-4000HC-6TG144I	4320	2.5 V / 3.3 V	-6	Halogen-Free TQFP	144	IND
LCMXO2-4000HC-4MG132I	4320	2.5 V / 3.3 V	-4	Halogen-Free csBGA	132	IND
LCMXO2-4000HC-5MG132I	4320	2.5 V / 3.3 V	-5	Halogen-Free csBGA	132	IND
LCMXO2-4000HC-6MG132I	4320	2.5 V / 3.3 V	-6	Halogen-Free csBGA	132	IND
LCMXO2-4000HC-4BG256I	4320	2.5 V / 3.3 V	-4	Halogen-Free caBGA	256	IND
LCMXO2-4000HC-5BG256I	4320	2.5 V / 3.3 V	-5	Halogen-Free caBGA	256	IND
LCMXO2-4000HC-6BG256I	4320	2.5 V / 3.3 V	-6	Halogen-Free caBGA	256	IND
LCMXO2-4000HC-4FTG256I	4320	2.5 V / 3.3 V	-4	Halogen-Free ftBGA	256	IND
LCMXO2-4000HC-5FTG256I	4320	2.5 V / 3.3 V	-5	Halogen-Free ftBGA	256	IND
LCMXO2-4000HC-6FTG256I	4320	2.5 V / 3.3 V	-6	Halogen-Free ftBGA	256	IND
LCMXO2-4000HC-4BG332I	4320	2.5 V / 3.3 V	-4	Halogen-Free caBGA	332	IND
LCMXO2-4000HC-5BG332I	4320	2.5 V / 3.3 V	-5	Halogen-Free caBGA	332	IND
LCMXO2-4000HC-6BG332I	4320	2.5 V / 3.3 V	-6	Halogen-Free caBGA	332	IND
LCMXO2-4000HC-4FG484I	4320	2.5 V / 3.3 V	-4	Halogen-Free fpBGA	484	IND
LCMXO2-4000HC-5FG484I	4320	2.5 V / 3.3 V	-5	Halogen-Free fpBGA	484	IND
LCMXO2-4000HC-6FG484I	4320	2.5 V / 3.3 V	-6	Halogen-Free fpBGA	484	IND

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-7000HC-4TG144I	6864	2.5 V / 3.3 V	-4	Halogen-Free TQFP	144	IND
LCMXO2-7000HC-5TG144I	6864	2.5 V / 3.3 V	-5	Halogen-Free TQFP	144	IND
LCMXO2-7000HC-6TG144I	6864	2.5 V / 3.3 V	-6	Halogen-Free TQFP	144	IND
LCMXO2-7000HC-4BG256I	6864	2.5 V / 3.3 V	-4	Halogen-Free caBGA	256	IND
LCMXO2-7000HC-5BG256I	6864	2.5 V / 3.3 V	-5	Halogen-Free caBGA	256	IND
LCMXO2-7000HC-6BG256I	6864	2.5 V / 3.3 V	-6	Halogen-Free caBGA	256	IND
LCMXO2-7000HC-4FTG256I	6864	2.5 V / 3.3 V	-4	Halogen-Free ftBGA	256	IND
LCMXO2-7000HC-5FTG256I	6864	2.5 V / 3.3 V	-5	Halogen-Free ftBGA	256	IND
LCMXO2-7000HC-6FTG256I	6864	2.5 V / 3.3 V	-6	Halogen-Free ftBGA	256	IND
LCMXO2-7000HC-4BG332I	6864	2.5 V / 3.3 V	-4	Halogen-Free caBGA	332	IND
LCMXO2-7000HC-5BG332I	6864	2.5 V / 3.3 V	-5	Halogen-Free caBGA	332	IND
LCMXO2-7000HC-6BG332I	6864	2.5 V / 3.3 V	-6	Halogen-Free caBGA	332	IND
LCMXO2-7000HC-4FG400I	6864	2.5 V / 3.3 V	-4	Halogen-Free fpBGA	400	IND
LCMXO2-7000HC-5FG400I	6864	2.5 V / 3.3 V	-5	Halogen-Free fpBGA	400	IND
LCMXO2-7000HC-6FG400I	6864	2.5 V / 3.3 V	-6	Halogen-Free fpBGA	400	IND
LCMXO2-7000HC-4FG484I	6864	2.5 V / 3.3 V	-4	Halogen-Free fpBGA	484	IND
LCMXO2-7000HC-5FG484I	6864	2.5 V / 3.3 V	-5	Halogen-Free fpBGA	484	IND
LCMXO2-7000HC-6FG484I	6864	2.5 V / 3.3 V	-6	Halogen-Free fpBGA	484	IND



High Performance Industrial Grade Devices Without Voltage Regulator, Halogen Free (RoHS) Packaging

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-2000HE-4TG100I	2112	1.2 V	-4	Halogen-Free TQFP	100	IND
LCMXO2-2000HE-5TG100I	2112	1.2 V	-5	Halogen-Free TQFP	100	IND
LCMXO2-2000HE-6TG100I	2112	1.2 V	-6	Halogen-Free TQFP	100	IND
LCMXO2-2000HE-4MG132I	2112	1.2 V	-4	Halogen-Free csBGA	132	IND
LCMXO2-2000HE-5MG132I	2112	1.2 V	-5	Halogen-Free csBGA	132	IND
LCMXO2-2000HE-6MG132I	2112	1.2 V	-6	Halogen-Free csBGA	132	IND
LCMXO2-2000HE-4TG144I	2112	1.2 V	-4	Halogen-Free TQFP	144	IND
LCMXO2-2000HE-5TG144I	2112	1.2 V	-5	Halogen-Free TQFP	144	IND
LCMXO2-2000HE-6TG144I	2112	1.2 V	-6	Halogen-Free TQFP	144	IND
LCMXO2-2000HE-4BG256I	2112	1.2 V	-4	Halogen-Free caBGA	256	IND
LCMXO2-2000HE-5BG256I	2112	1.2 V	-5	Halogen-Free caBGA	256	IND
LCMXO2-2000HE-6BG256I	2112	1.2 V	-6	Halogen-Free caBGA	256	IND
LCMXO2-2000HE-4FTG256I	2112	1.2 V	-4	Halogen-Free ftBGA	256	IND
LCMXO2-2000HE-5FTG256I	2112	1.2 V	-5	Halogen-Free ftBGA	256	IND
LCMXO2-2000HE-6FTG256I	2112	1.2 V	-6	Halogen-Free ftBGA	256	IND

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-2000UHE-4FG484I	2112	1.2 V	-4	Halogen-Free fpBGA	484	IND
LCMXO2-2000UHE-5FG484I	2112	1.2 V	-5	Halogen-Free fpBGA	484	IND
LCMXO2-2000UHE-6FG484I	2112	1.2 V	-6	Halogen-Free fpBGA	484	IND